

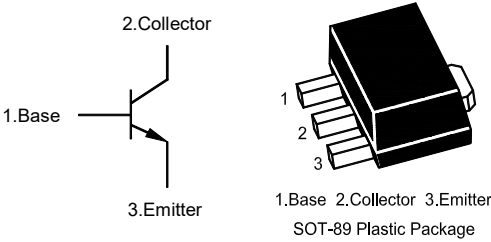
BCX54U-CH

NPN Silicon Epitaxial Planar Power Transistor

Medium Power Transistor

Features

- AEC-Q101 Qualified
- Halogen and Antimony Free(HAF), RoHS compliant



Absolute Maximum Ratings (T_a = 25°C)

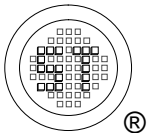
Parameter	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	45	V
Collector Emitter Voltage	V _{CEO}	45	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	I _C	1	A
Peak Collector Current	I _{CM}	1.5	A
Peak Base Current	I _{BM}	0.2	A
Total Power Dissipation	P _{tot}	0.5 ¹⁾ 1.3 ²⁾	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient	R _{θJA}	250 ¹⁾ 96 ²⁾	°C/W

¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

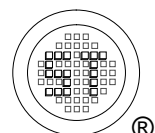
²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.



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Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $V_{CE} = 2\text{ V}$, $I_C = 5\text{ mA}$	h_{FE}	63	-	-	-
at $V_{CE} = 2\text{ V}$, $I_C = 150\text{ mA}$	h_{FE}	63	-	160	-
BCX54-10U	h_{FE}	100	-	250	-
BCX54-16U	h_{FE}	40	-	-	-
at $V_{CE} = 2\text{ V}$, $I_C = 500\text{ mA}$	h_{FE}	40	-	-	-
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	45	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	45	-	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$	-	-	0.5	V
Base Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{BE(sat)}$	-	-	1.1	V
Base Emitter Voltage at $V_{CE} = 2\text{ V}$, $I_C = 500\text{ mA}$	V_{BE}	-	-	1	V
Transition Frequency at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	130	-	MHz



Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

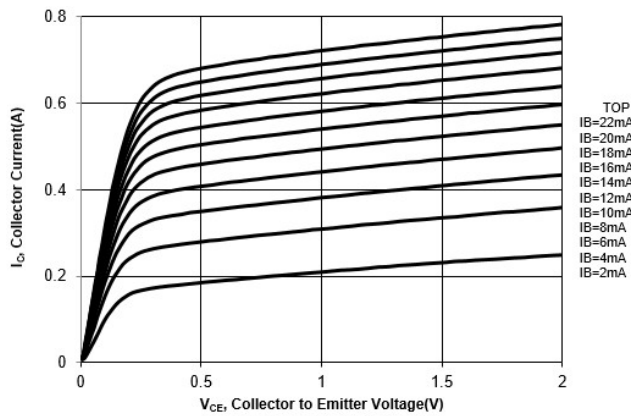


Fig. 2 Collector Current vs. Base to Emitter Voltage

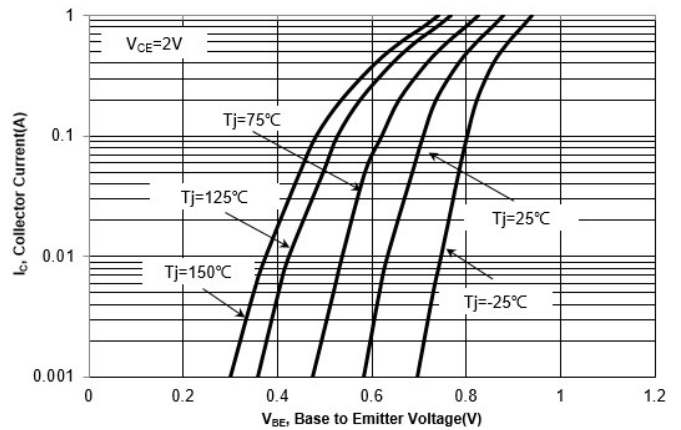


Fig. 3 DC Current Gain vs. Collector Current

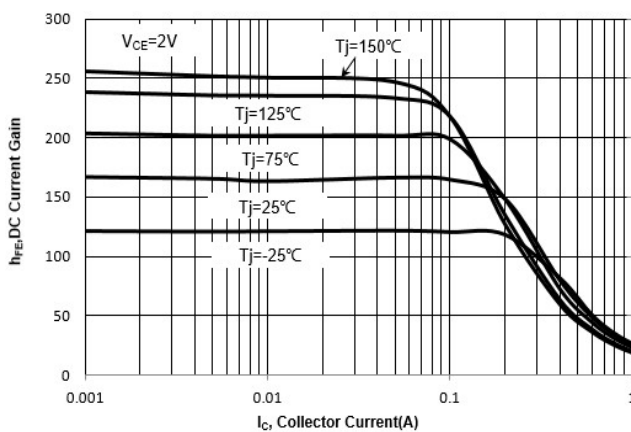
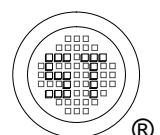
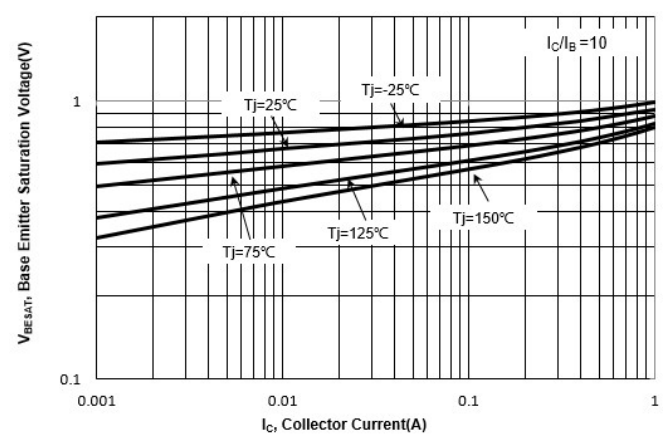


Fig. 4 $V_{BE(sat)}$ vs. Collector Current



Electrical Characteristics Curves

Fig. 5 $V_{CE(sat)}$ vs. Collector Current

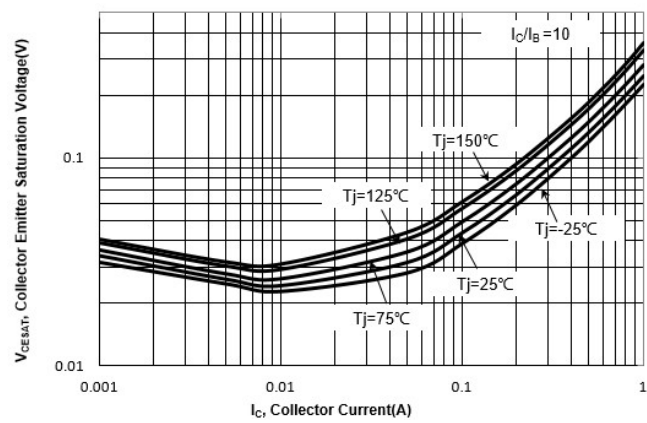


Fig. 6 Output Capacitance

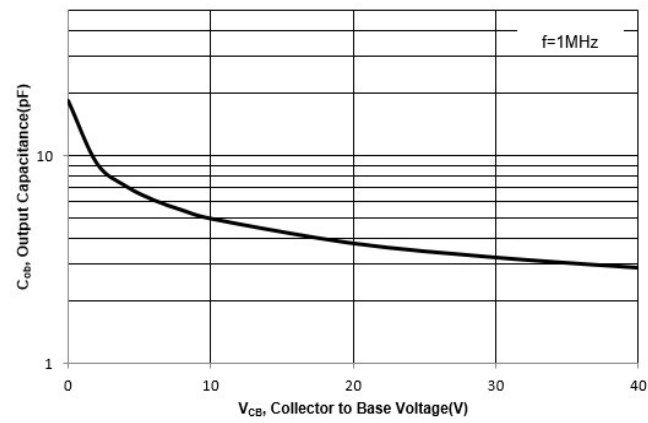
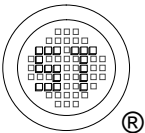
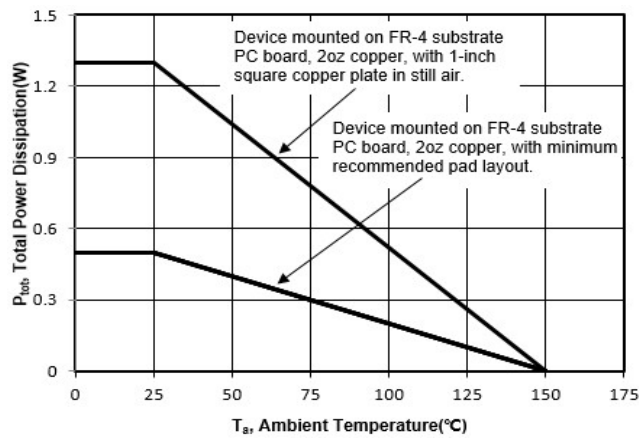


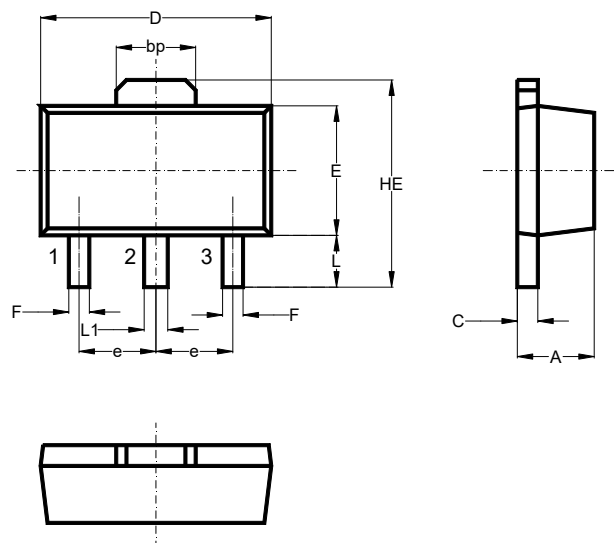
Fig. 7 Power Derating Curve



BCX54U-CH

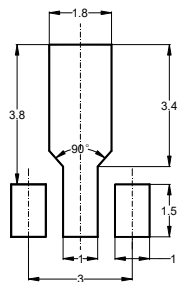
Package Outline (Dimensions in mm)

SOT-89



Unit	A	bp	C	D	E	F	HE	e	L	L1
mm	1.6	1.60	0.5	4.6	2.6	0.45	4.25	1.5	1.05	0.51
	1.4	1.50	0.3	4.4	2.4	0.35	3.75	typ.	0.95	0.41

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-89	12	8 ± 0.1	0.315 ± 0.004	178	7	1,000
				330	13	4,000

Marking information

" BCX54-**U " = Part No. (" ** " = HFE grouping Code)

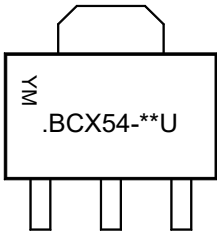
" • " = HAF (Halogen and Antimony Free)

" YM " = Date Code Marking

" Y " = Year

" M " = Month

Font type: Arial



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